

SCHOTTKY DIODES

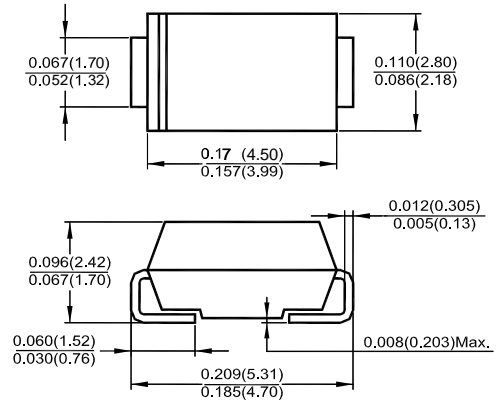
SS22---SS2200

FEATURES

- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- The plastic package carries Underwriters Laboratory flammability Classification 94V-0
- High forward surge current capability
- Built-in strain relief, ideal for automated placement

MECHANICAL DATA

- SMA (DO-214AC) molded plastic
- Polarity: Color band denotes cathode end



Dimensions in inches and (millimeters)
DO-214AC (SMA)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

MDD Catalog Number	SYMBOLS	SS22	SS23	SS24	SS25	SS26	SS28	SS210	SS2150	SS2200	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	VOLTS
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	VOLTS
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	VOLTS
Maximum average forward rectified current at T_L (see fig.1)	$I_{(AV)}$	2.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50.0									Amps
Maximum instantaneous forward voltage at 2.0A	V_F	0.55		0.70		0.85		0.95			Volts
Maximum DC reverse current at rated DC blocking voltage	I_R	0.5						0.2			mA
$T_A=25^{\circ}C$ $T_A=100^{\circ}C$		10.0			5.0		2.0				
Typical junction capacitance (NOTE 1)	C_J	220			180						pF
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	75.0									$^{\circ}C/W$
Operating junction temperature range	T_J	-50 to +125					-50 to +150				$^{\circ}C$
Storage temperature range	T_{STG}	-50 to +150									$^{\circ}C$

Note:1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

SS22---SS2200 Typical Characteristics

